H8 95 Run Plan		Update: 95/8/10
Variables	**Range**	**Motivation**
Bias voltage	Under-Depletion, Dep+50V (20Vstep,10V@high-end	Charge collection
Threshold	0.6-1.4fC(0.2fCstep),1.7fC,2-4fC(0.5fC),5fC,6fC	Eff-Noise, Median
phi-rotation	0 - atan(pitch/thickness)+some (atan(pitch/thickness)=9.5°(50µm), 14°(75µm))	Charge sharing
theta-rotatior	0, 30, 60°	Dynamic range
Scan along strip (y):	Far, near, on-hybrid	Strip resistance

Variable		#points
Bias voltage	40,60,80,100,110,120	6
Threshold	0.6,0.8,1.0,1.2,1.4,1.7,2.0,2.5,3.0,3.5,4.0,5.0,6.0	13
Phi-rotation	0,7,14,21 (only for 75µm)	4
Theta-rot.	none	
y-scan	0.5, 3, 5.5, 8.0	4

Run time estimation

Trigger rate	170events/spill Spill=2sec Repetition=14.4sec <average rate>=170/14.4=11.8 Hz->10Hz (least?)	
Trigger area	1cm(H)x3cm(V)	
No. events	Occupancy=0.2x10^-4->50k events->80min(@0.8,1.0,1.2,1.4fC) Eff.error=~1%(eff=0.5)->1k events ->1k/(all accep~0.1)=10k->15min	
Thresh.scan	Eff.scan=13x15min=	3.3 hrs
	Eff-Occupancy scan=9x15min+4x80min=	7.6 hrs

y [cm]	phi [°]	theta [°]	V_bias [V]	V_th [fC]	Run time [hrs]	[days]
1st path	phi-rotation					
5.5	0	0	100	0.6-6	7.6	Eff-Occ scan
	7		100	0.6-6	3.3	
	14		100	0.6-6	3.3	
	21		100	0.6-6	3.3	
2nd path			Bias scan	Expected depletion voltage=70V		
5.5	0	0	40	0.6-6	3.3	Eff scan
			60		3.3	
			80		3.3	
			100		7.6	Eff-Occ scan
			110		3.3	
			120		7.6	Eff-Occ scan
0.5	0	0	60-120	0.6-6	16.5	Eff scan
3rd path	position scan					
3	0	0	100	0.6-6	3.3	
8				0.6-6	3.3	
Total					69.0	2.9
with 50% duty					138.0	5.8